NEWHAVEN DISPLAY INTERNATIONAL

Product Specification

NHD-2.8-CSXP-BREAKOUT

TFT Liquid Crystal Display

NHD-	Newhaven Display
2.8-	2.8" Diagonal
C-	Built-in Controller
S-	High Brightness, White LED Backlight
X-	TFT
P-	IPS, Wide Temperature
BREAKOUT-	Breakout Board

Newhaven Display International, Inc.
2661 Galvin Court, Elgin, IL 60124 USA

Ph: 847.844.8795 | Fx: 847.844.8796
www.newhavendisplay.com

REACH Compliant

RoHS Compliant

NEWHAVEN DISPLAY INTERNATIONAL

Table of Contents

Document Revision History 2
Mechanical Drawing 3
Pin Description 4
Interface Selection 4
Electrical Characteristics 5
Optical Characteristics 5
Controller Information 5
Table of Commands 5
Timing Characteristics for TFT 6
Example Initialization Code 10
Quality Information 12

Additional Resources

- **Support Forum:** https://support.newhavendisplay.com/hc/en-us/community/topics
- **GitHub:** https://github.com/newhavendisplay
- **Example Code:** https://support.newhavendisplay.com/hc/en-us/categories/4409527834135-Example-Code/
- **Knowledge Center:** https://www.newhavendisplay.com/knowledge_center.html
- **Quality Center:** https://www.newhavendisplay.com/quality_center.html
- **Precautions for using LCDs/LCMs:** https://www.newhavendisplay.com/specs/precautions.pdf
- **Warranty / Terms & Conditions:** https://www.newhavendisplay.com/terms.html

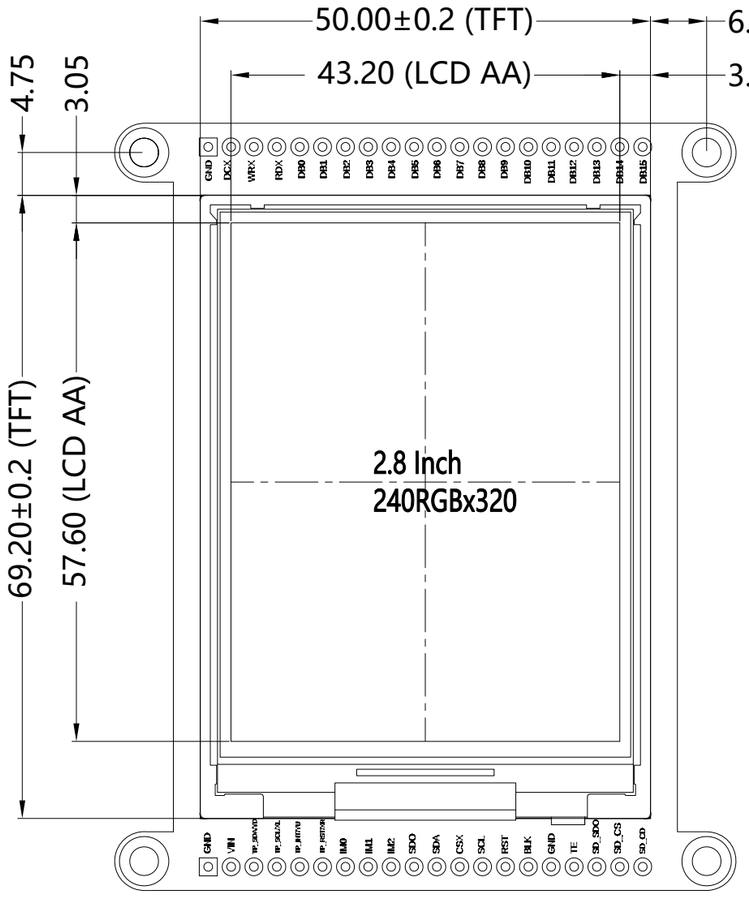
Document Revision History

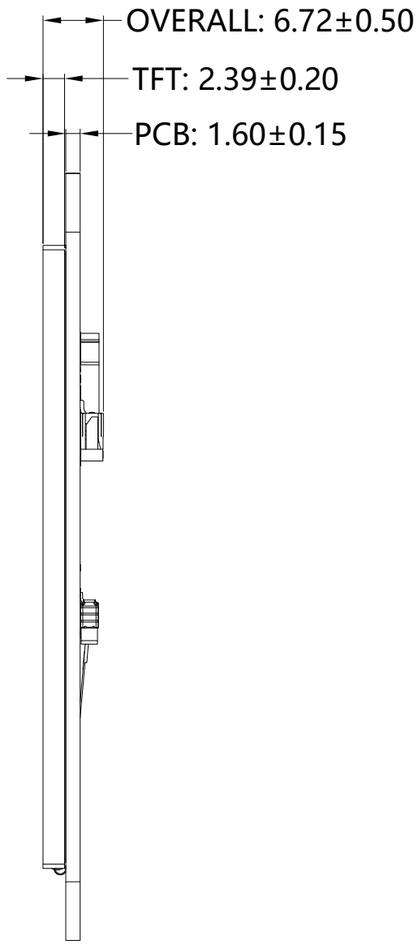
Revision	Date	Description	Changed By
-	11/12/2025	Initial Release	KL

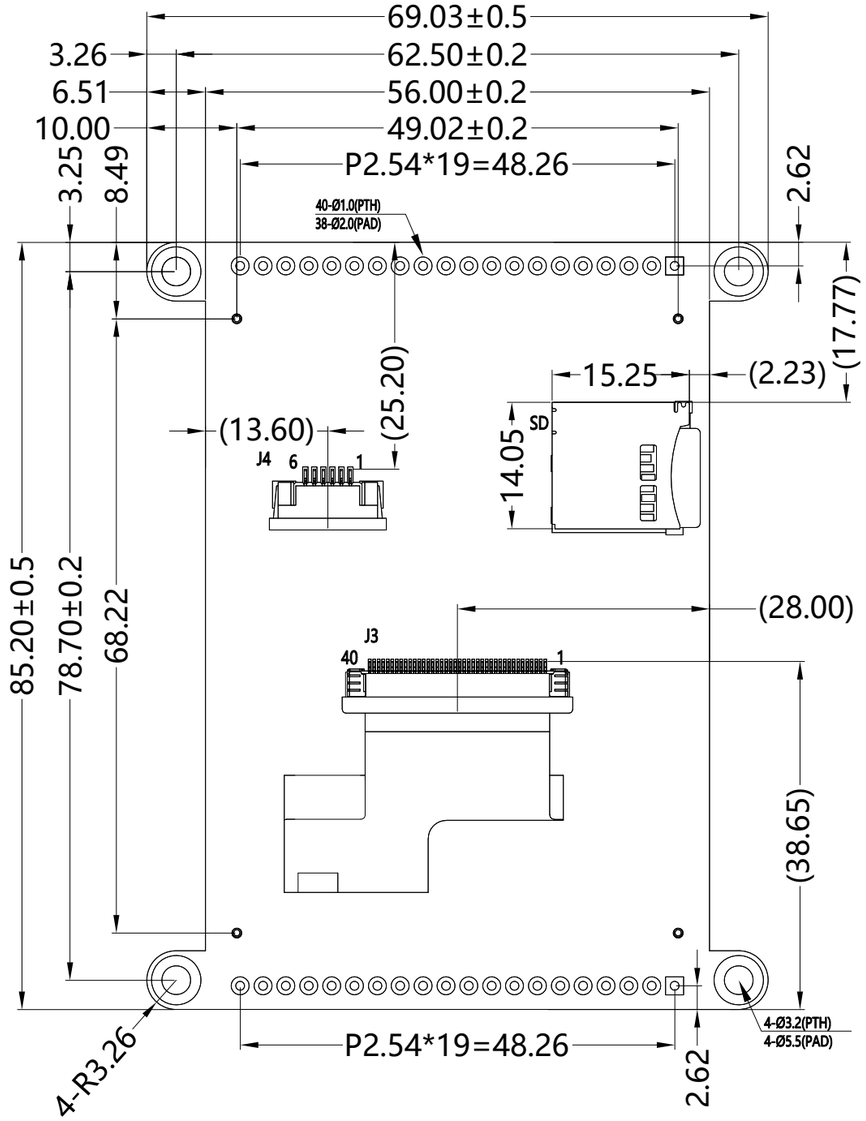
Mechanical Drawing

Newhaven Display
NHD-2.8-CSXP-BREAKOUT
Date Code

Part Label (type/format may vary)







Product Description: 2.8” 240x320 IPS TFT w/Breakout PCB

1. Driver IC: ST7789VI
2. Interface: Parallel, SPI
3. Power Requirement: 3.3/5.0V
4. Optical Features: Normally Black, Transmissive, Anti-Glare, 1000cd/m²
5. Key Features: EMI Shielding, Backlight Driver, microSD Card Reader, Mounting Holes

Standard Tolerance: (Unless otherwise specified) Linear: ±0.3mm	NEWHAVEN DISPLAY INTERNATIONAL	
	Drawing/Part Number: NHD-2.8-CSXP-BREAKOUT	Revision: -
Unless otherwise specified: • Dimensions are in Millimeters • Third Angle Projection	Drawn By: K. Lewis	Approved By: K. Lewis
	Drawn Date: 11/12/2025	Approved Date: 11/12/2025

This drawing is solely the property of Newhaven Display International, Inc. The information it contains is not to be disclosed, reproduced or copied in whole or part without written approval from Newhaven Display.

Pin Description

J1:

Pin No.	Symbol	External Connection	Function Description
1	GND	Power Supply	Ground
2	DCX	MPU	Data / Command selection: '1' = Data ; '0' = Command
3	WRX	MPU	Active LOW Write signal
4	RDX	MPU	Active LOW Read signal
5-20	DB0-DB15	MPU	Bi-directional data bus 8-bit: use DB8-DB15 16-bit: use DB0-DB15

Recommended Connector: 20pin, 1x20, 2.54mm pitch.

J2:

Pin No.	Symbol	External Connection	Function Description
1	GND	Power Supply	Ground
2	VIN	Power Supply	Supply Voltage (3.3V or 5V)
3	TP_SDA/YD	MPU	No Connect
4	TP_SCL/XL		
5	TP_INT/YU		
6	TP_RST/XR		
7	IM0	MPU	No Connect
8	IM1		No Connect
9	IM2		No Connect
10	SDO	MPU	Serial Data Output
11	SDA	MPU	Serial Data Input
12	CSX	MPU	Active LOW Chip Select signal
13	SCL	MPU	Serial Clock
14	RST	MPU	Active LOW Reset signal
15	BLK	MPU	No Connect
16	GND	Power Supply	Ground
17	TE	MPU	Tearing Effect Output
18	SD_SDO	MPU	SD card Serial Data Output
19	SD_CS	MPU	SD card Chip select Signal
20	SD_CD	MPU	SD Card Detect Pin

Recommended Connector: 20pin, 1x20, 2.54mm pitch.

Interface Selection

Interface	IM0		IM1		IM2	
	R1	R2	R3	R4	R5	R6
8-bit 8080-II Parallel (default)	Close	Open	Open	Close	Open	Close
16-bit 8080-II Parallel	Open	Close	Open	Close	Open	Close
3-wire SPI	Close	Open	Open	Close	Close	Open
4-wire SPI	Open	Close	Close	Open	Close	Open

Electrical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Operating Temperature Range	T_{OP}	Absolute Max	-20	-	+70	°C
Storage Temperature Range	T_{ST}	Absolute Max	-30	-	+80	°C
Supply Voltage for LCD	V_{DD}	-	3.3	-	5.5	V
Supply Current	I_{DD}	V_{DD} = 5.0V	-	200	280	mA

Optical Characteristics

Item		Symbol	Condition	Min.	Typ.	Max.	Unit
Optimal Viewing Angles	Top	φY+	CR ≥ 10	-	80	-	°
	Bottom	φY-		-	80	-	°
	Left	θX-		-	80	-	°
	Right	θX-		-	80	-	°
Contrast Ratio		CR	-	600	800	-	-
Luminance		L_V	I_{LED} = 160 mA	800	1000	-	cd/m^2
Response Time		$T_R + T_F$	T_{OP} = 25°C	-	30	40	ms
Chromaticity	Red	X_R	-	0.58	0.62	0.66	-
		Y_R	-	0.29	0.33	0.37	-
	Green	X_G	-	0.26	0.30	0.34	-
		Y_G	-	0.56	0.60	0.64	-
	Blue	X_B	-	0.11	0.15	0.19	-
		Y_G	-	0.01	0.05	0.09	-
	White	X_W	-	0.23	0.27	0.31	-
		Y_W	-	0.24	0.28	0.32	-

Controller Information

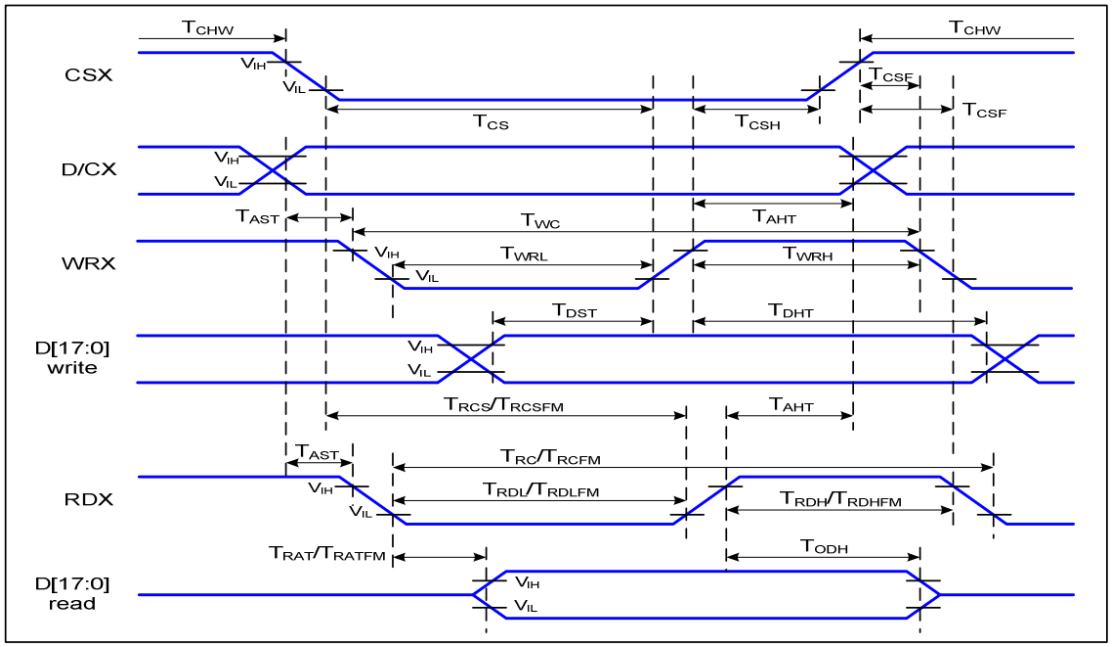
Built-in ST7789VI Controller: https://support.newhavendisplay.com/hc/en-us/articles/10814990300823-ST7789VI

Table of Commands

Please download specification at: http://www.newhavendisplay.com/appnotes/datasheets/LCDs/ST7789V.pdf

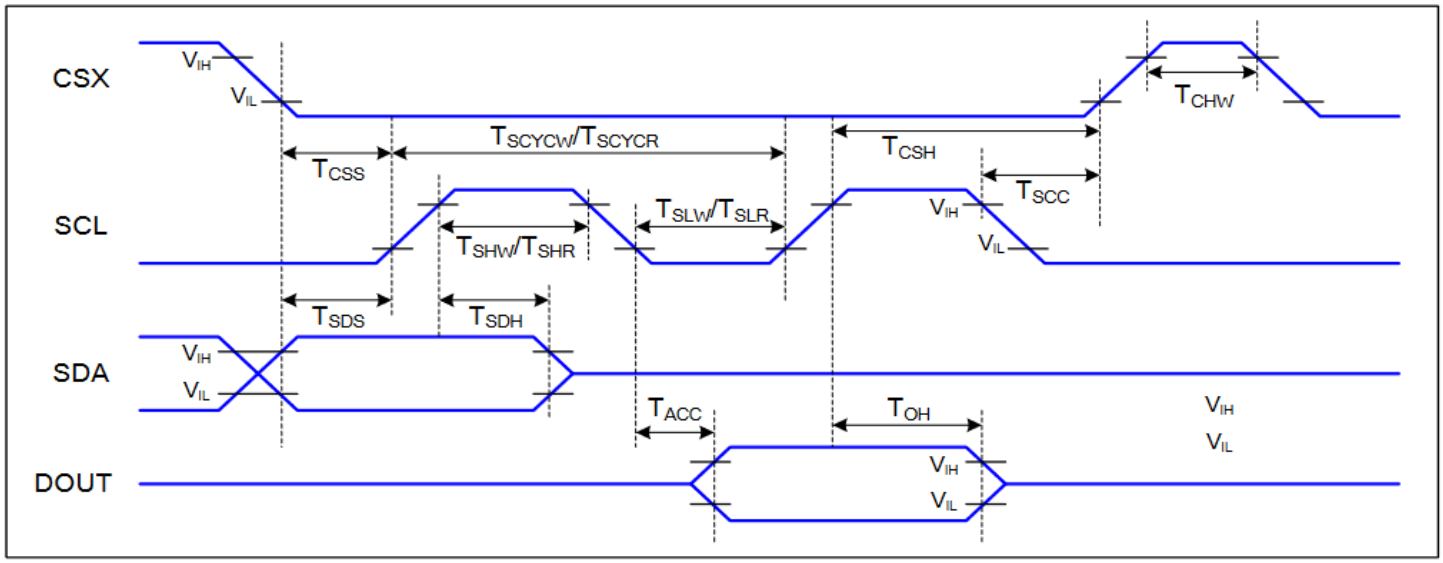
Timing Characteristics for TFT

Parallel 8/16-bit Interface Timing Characteristics (8080-II system)



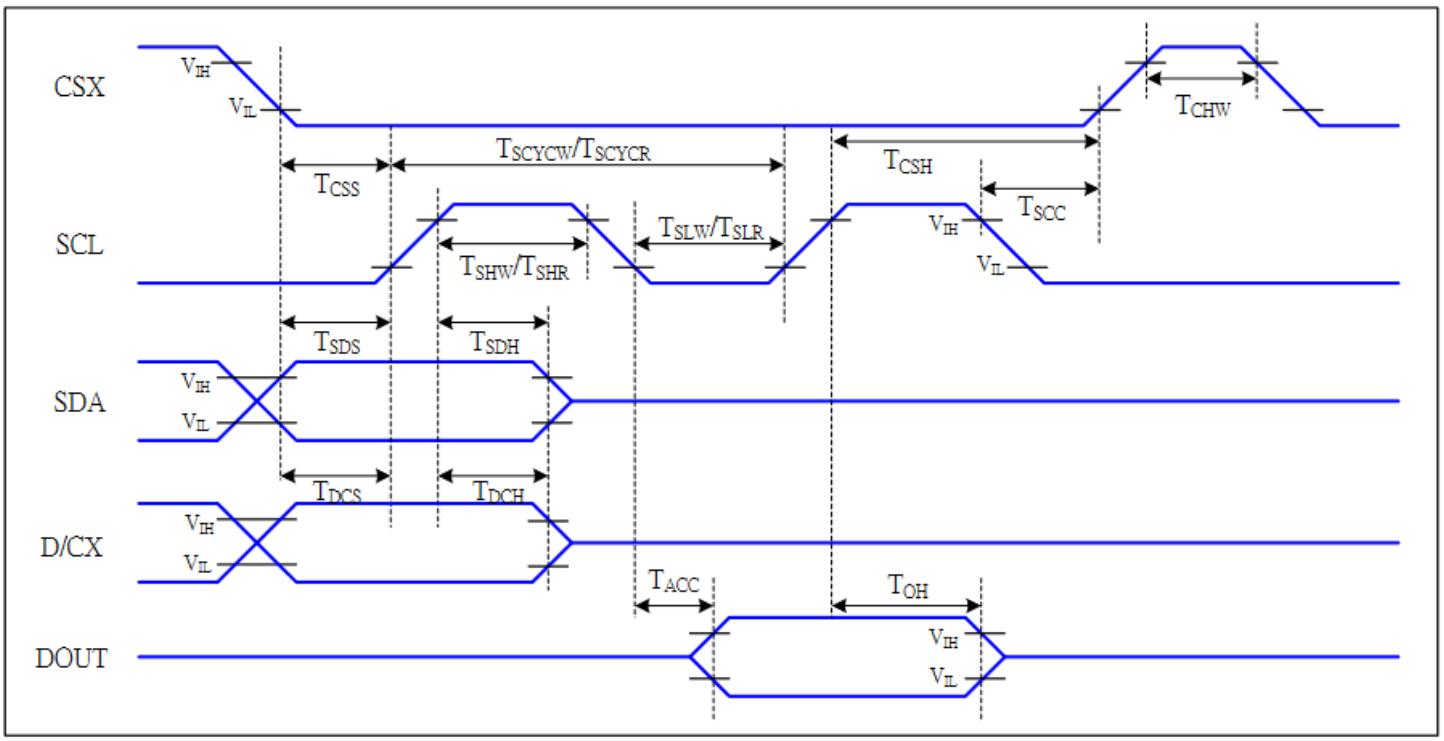
Signal	Symbol	Parameter	Min	Max	Unit	Description
D/CX	T_{AST}	Address setup time	0		ns	-
	T_{AHT}	Address hold time (Write/Read)	10		ns	
CSX	T_{CHW}	Chip select "H" pulse width	0		ns	-
	T_{CS}	Chip select setup time (Write)	15		ns	
	T_{RCS}	Chip select setup time (Read ID)	45		ns	
	T_{RCSFM}	Chip select setup time (Read FM)	355		ns	
	T_{CSF}	Chip select wait time (Write/Read)	10		ns	
	T_{CSH}	Chip select hold time	10		ns	
WRX	T_{WC}	Write cycle	66		ns	
	T_{WRH}	Control pulse "H" duration	15		ns	
	T_{WRL}	Control pulse "L" duration	15		ns	
RDX (ID)	T_{RC}	Read cycle (ID)	160		ns	When read ID data
	T_{RDH}	Control pulse "H" duration (ID)	90		ns	
	T_{RDL}	Control pulse "L" duration (ID)	45		ns	
RDX (FM)	T_{RCFM}	Read cycle (FM)	450		ns	When read from frame memory
	T_{RDHFM}	Control pulse "H" duration (FM)	90		ns	
	T_{RDLFM}	Control pulse "L" duration (FM)	355		ns	
D[17:0]	T_{DST}	Data setup time	10		ns	For CL=30pF
	T_{DHT}	Data hold time	10		ns	
	T_{RAT}	Read access time (ID)		40	ns	
	T_{RATFM}	Read access time (FM)		340	ns	
	T_{ODH}	Output disable time	20	80	ns	

3-wire SPI



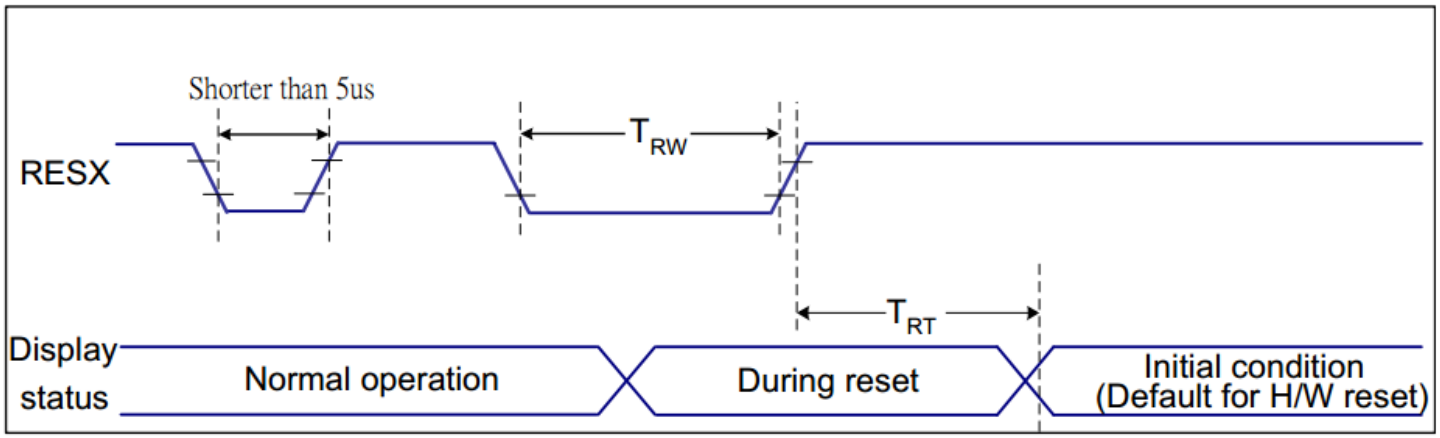
Signal	Symbol	Parameter	Min	Max	Unit	Description
CSX	T_{CSS}	Chip select setup time (write)	15		ns	
	T_{CSH}	Chip select hold time (write)	15		ns	
	T_{CSS}	Chip select setup time (read)	60		ns	
	T_{SCC}	Chip select hold time (read)	65		ns	
	T_{CHW}	Chip select “H” pulse width	40		ns	
SCL	T_{SCYCW}	Serial clock cycle (Write)	16		ns	
	T_{SHW}	SCL “H” pulse width (Write)	7		ns	
	T_{SLW}	SCL “L” pulse width (Write)	7		ns	
	T_{SCYCR}	Serial clock cycle (Read)	150		ns	
	T_{SHR}	SCL “H” pulse width (Read)	60		ns	
	T_{SLR}	SCL “L” pulse width (Read)	60		ns	
SDA (DIN)	T_{SDS}	Data setup time	7		ns	
	T_{SDH}	Data hold time	7		ns	
DOUT	T_{ACC}	Access time	10	50	ns	For maximum CL=30pF
	T_{OH}	Output disable time	15	50	ns	For minimum CL=8pF

4-wire SPI



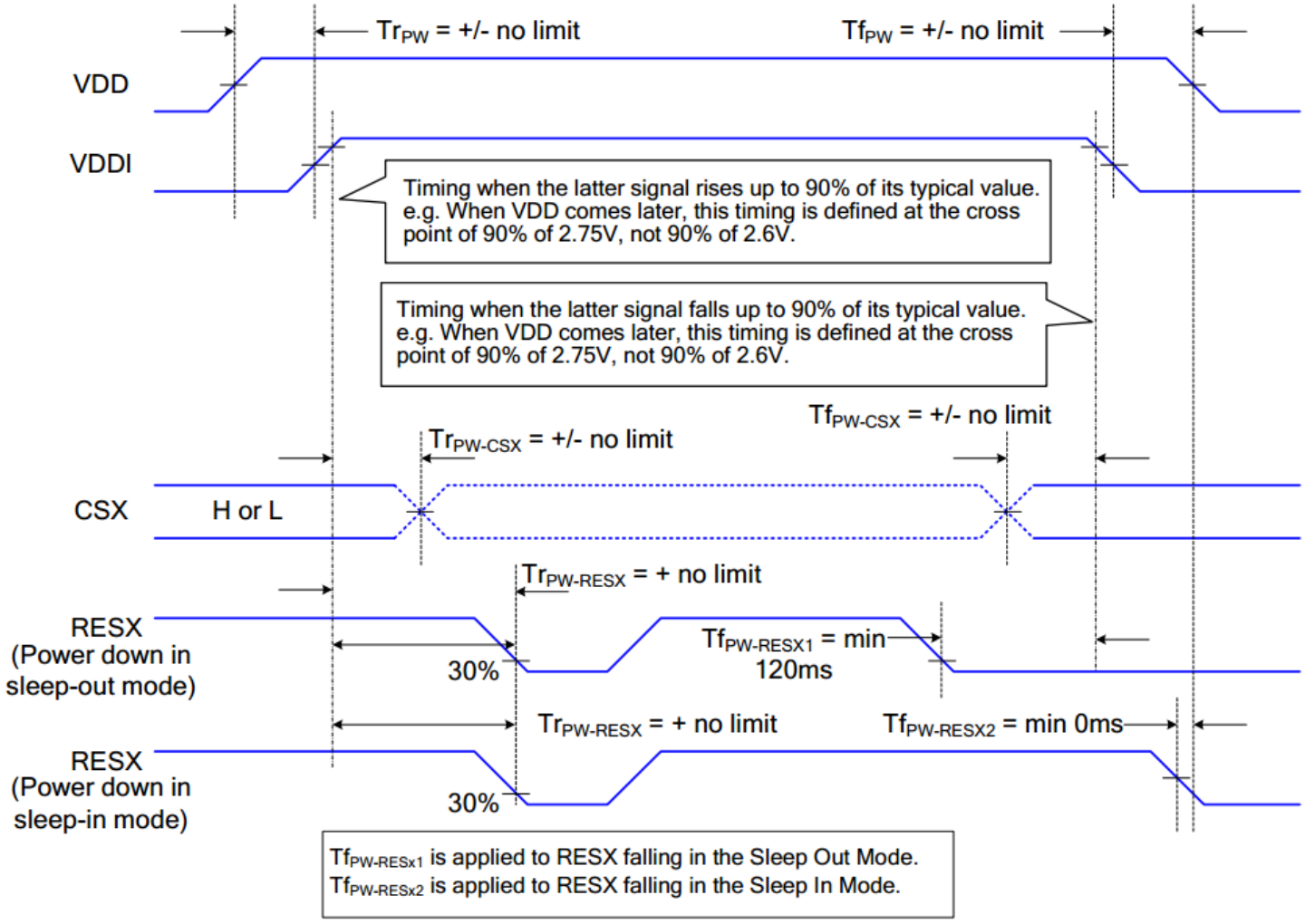
Signal	Symbol	Parameter	MIN	MAX	Unit	Description
CSX	T_{CSS}	Chip select setup time (write)	15		ns	
	T_{CSH}	Chip select hold time (write)	15		ns	
	T_{CSS}	Chip select setup time (read)	60		ns	
	T_{SCC}	Chip select hold time (read)	65		ns	
	T_{CHW}	Chip select “H” pulse width	40		ns	
SCL	T_{SCYCW}	Serial clock cycle (Write)	16		ns	-write command & data ram
	T_{SHW}	SCL “H” pulse width (Write)	7		ns	
	T_{SLW}	SCL “L” pulse width (Write)	7		ns	
	T_{SCYCR}	Serial clock cycle (Read)	150		ns	-read command & data ram
	T_{SHR}	SCL “H” pulse width (Read)	60		ns	
	T_{SLR}	SCL “L” pulse width (Read)	60		ns	
D/CX	T_{DCS}	D/CX setup time	10		ns	
	T_{DCH}	D/CX hold time	10		ns	
SDA (DIN)	T_{SDS}	Data setup time	7		ns	
	T_{SDH}	Data hold time	7		ns	
DOUT	T_{ACC}	Access time	10	50	ns	For maximum CL=30pF
	T_{OH}	Output disable time	15	50	ns	For minimum CL=8pF

Reset Timing



Related Pins	Symbol	Parameter	MIN	MAX	Unit
RESX	TRW	Reset pulse duration	10	-	us
	TRT	Reset cancel	-	5 (Note 1, 5)	ms
				120 (Note 1, 6, 7)	ms

Power ON/OFF Sequence



Example Initialization Code

```
/*************************************************************************/
void TFT_28_7789_Write_Command(unsigned int command)
{
GPIO_ResetBits(GPIOC, CS1);
GPIO_ResetBits(GPIOC, RS);
GPIO_SetBits(GPIOC, nRD);
GPIO_ResetBits(GPIOC, nWR);
GPIO_Write(GPIOB, command);
TFT_delay(10);
GPIO_SetBits(GPIOC, nWR);
TFT_delay(1);
}
/*************************************************************************/
void TFT_28_7789_Write_Data(unsigned int data1)
{
GPIO_Write(GPIOB, data1);
GPIO_SetBits(GPIOC, RS);
GPIO_ResetBits(GPIOC, nWR);
TFT_delay(1);
GPIO_SetBits(GPIOC, nWR);
}
/*************************************************************************/
void TFT_28_7789_Init(void)
{
GPIO_ResetBits(GPIOC, CS1);
GPIO_SetBits(GPIOC, nRD);
GPIO_ResetBits(GPIOC, nWR);
GPIO_WriteBit(GPIOC, RES, Bit_RESET);
TFT_delay(100);
GPIO_WriteBit(GPIOC, RES, Bit_SET);
TFT_delay(100);
TFT_28_7789_Write_Command(0x0011);//exit SLEEP mode
TFT_delay(100);

TFT_28_7789_Write_Command(0x0036);
TFT_28_7789_Write_Data(0x0080);//MADCTL: memory data access control
TFT_28_7789_Write_Command(0x003A);
TFT_28_7789_Write_Data(0x0066);//COLMOD: Interface Pixel format
TFT_28_7789_Write_Command(0x0021);//INVON: Display Inversion ON (setting for IPS)
TFT_28_7789_Write_Command(0x00B2);
TFT_28_7789_Write_Data(0x000C);
TFT_28_7789_Write_Data(0x0C);
TFT_28_7789_Write_Data(0x00);
TFT_28_7789_Write_Data(0x33);
TFT_28_7789_Write_Data(0x33);//PORCTRK: Porch setting
TFT_28_7789_Write_Command(0x00B7);
TFT_28_7789_Write_Data(0x0035);//GCTRL: Gate Control
TFT_28_7789_Write_Command(0x00BB);
TFT_28_7789_Write_Data(0x002B);//VCOMS: VCOM setting
TFT_28_7789_Write_Command(0x00C0);
TFT_28_7789_Write_Data(0x002C);//LCMCTRL: LCM Control
TFT_28_7789_Write_Command(0x00C2);
TFT_28_7789_Write_Data(0x0001);
TFT_28_7789_Write_Data(0xFF);//VDVVRHEN: VDV and VRH Command Enable
TFT_28_7789_Write_Command(0x00C3);
TFT_28_7789_Write_Data(0x0011);//VRHS: VRH Set
TFT_28_7789_Write_Command(0x00C4);
TFT_28_7789_Write_Data(0x0020);//VDVS: VDV Set
```

```
TFT_28_7789_Write_Command(0x00C6);
TFT_28_7789_Write_Data(0x000F);//FRCTRL2: Frame Rate control in normal mode
TFT_28_7789_Write_Command(0x00D0);
TFT_28_7789_Write_Data(0x00A4);
TFT_28_7789_Write_Data(0xA1);//PWCTRL1: Power Control 1
TFT_28_7789_Write_Command(0x00E0);
TFT_28_7789_Write_Data(0x00D0);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0005);
TFT_28_7789_Write_Data(0x000E);
TFT_28_7789_Write_Data(0x0015);
TFT_28_7789_Write_Data(0x000D);
TFT_28_7789_Write_Data(0x0037);
TFT_28_7789_Write_Data(0x0043);
TFT_28_7789_Write_Data(0x0047);
TFT_28_7789_Write_Data(0x0009);
TFT_28_7789_Write_Data(0x0015);
TFT_28_7789_Write_Data(0x0012);
TFT_28_7789_Write_Data(0x0016);
TFT_28_7789_Write_Data(0x0019);//PVGAMCTRL: Positive Voltage Gamma control
TFT_28_7789_Write_Command(0x00E1);
TFT_28_7789_Write_Data(0x00D0);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0005);
TFT_28_7789_Write_Data(0x000D);
TFT_28_7789_Write_Data(0x000C);
TFT_28_7789_Write_Data(0x0006);
TFT_28_7789_Write_Data(0x002D);
TFT_28_7789_Write_Data(0x0044);
TFT_28_7789_Write_Data(0x0040);
TFT_28_7789_Write_Data(0x000E);
TFT_28_7789_Write_Data(0x001C);
TFT_28_7789_Write_Data(0x0018);
TFT_28_7789_Write_Data(0x0016);
TFT_28_7789_Write_Data(0x0019);//NVGAMCTRL: Negative Voltage Gamma control
TFT_28_7789_Write_Command(0x002A);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x00EF);//X address set
TFT_28_7789_Write_Command(0x002B);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0000);
TFT_28_7789_Write_Data(0x0001);
TFT_28_7789_Write_Data(0x003F);//Y address set

TFT_delay(10);
}
/*****************************************************************************/
```

Quality Information

Test Item	Content of Test	Test Condition	Note
High Temperature Storage	Endurance test applying the high storage temperature for a long time.	+80°C, 240hrs	2
Low Temperature Storage	Endurance test applying the low storage temperature for a long time.	-30°C, 240hrs	1,2
High Temperature Operation	Endurance test applying the electric stress (voltage & current) and the high thermal stress for a long time.	+70°C, 120hrs	2
Low Temperature Operation	Endurance test applying the electric stress (voltage & current) and the low thermal stress for a long time.	-20°C, 120hrs	1,2
High Temperature / Humidity Operation	Endurance test applying the electric stress (voltage & current) and the high thermal with high humidity stress for a long time.	+50°C, 90% RH, 120hrs	1,2
Thermal Shock resistance	Endurance test applying the electric stress (voltage & current) during a cycle of low and high thermal stress.	-30°C 30min -> 25°C 10min -> 80°C 30min = 1 cycle. For 10 cycles	
Vibration test	Endurance test applying vibration to simulate transportation and use.	Frequency: 250 r/min Amplitude: 1 inch Time: 45min	3
Static electricity test	Endurance test applying electric static discharge.	Air discharge: ±8kV 10 Times Contact discharge: ±4kV 10 Times	

Note 1: No condensation to be observed.
Note 2: Conducted after 4 hours of storage at 25°C, 0%RH.
Note 3: Test performed on product itself, not inside a container.